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AMENDMENTS TO THE CLAIMS:

Please cancel claims 8-11, 24 and 30-31 without prejudice or disclaimer.

1. (Currently amended) A semiconductor device comprising:
a substrate;
an undercoat layer formed on said substrate and comprising a metal nitride; and
a group III nitride compound semiconductor layer formed on said undercoat layer, and
separated from said substrate by at least said undercoat layer,
wherein said metal nitride comprises at least one of Nb, V, Y, and Cr.
2. (Previously presented) A semiconductor device according to claim 1, wherein said metal nitride directly contacts said group III nitride compound semiconductor layer.
3. (Canceled)
4. (Previously presented) A semiconductor device according to claim 1, wherein said undercoat layer comprises at least one member selected from the group consisting of titanium nitride, zirconium nitride, hafnium nitride, tantalum nitride, and a nitride of a metal alloy.
5. (Previously presented) A semiconductor device according to claim 1, wherein said substrate comprises one member selected from the group consisting of sapphire, silicon carbide, gallium nitride, silicon, gallium phosphide, and gallium arsenide.
6. (Previously presented) A semiconductor device according to claim 1, wherein said substrate comprises a cubic crystal material comprising a (111) face on which said undercoat layer is formed.
7. - 19. (Canceled)

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20. (Previously presented) A semiconductor device according to claim 1, further comprising:

a first electrode provided on said undercoat layer.

21. - 22. (Canceled)

23. (Previously presented) A semiconductor device according to claim 1, wherein said undercoat layer is selected for providing a predetermined crystallinity of said group III nitride compound semiconductor layer.

24. (Canceled)

25. (Previously presented) A semiconductor device according to claim 1, wherein said undercoat layer has a thickness in a range of 0.1 to 10 μm .

26. (Previously presented) A semiconductor device according to claim 1, further comprising:

a metal layer adjacent to said undercoat layer.

27. (Previously presented) A semiconductor device according to claim 1, wherein said group III nitride compound semiconductor layer comprises a light-emitting layer.

28. (Previously presented) A semiconductor device according to claim 27, wherein said undercoat layer reflects light emitted from said light-emitting layer.

29. (Previously presented) A semiconductor device according to claim 1, wherein said undercoat layer comprises a continuously-formed undercoat layer.

30. - 31. (Canceled)